# 74VHC32-Q100; 74VHCT32-Q100 Quad 2-input OR gate

Rev. 1 — 20 December 2013

**Product data sheet** 

#### 1. **General description**

The 74VHC32-Q100; 74VHCT32-Q100 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard No. 7-A.

The 74VHC32-Q100; 74VHCT32-Q100 provide the 2-input OR function.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### **Features and benefits** 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V<sub>CC</sub>
- Input levels:
  - ◆ The 74VHC32-Q100 operates with CMOS input level
  - ◆ The 74VHCT32-Q100 operates with TTL input level
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Multiple package options

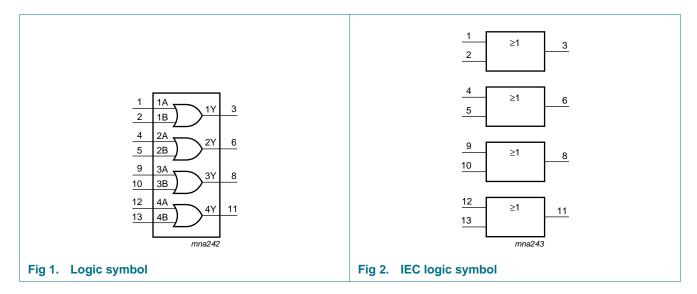


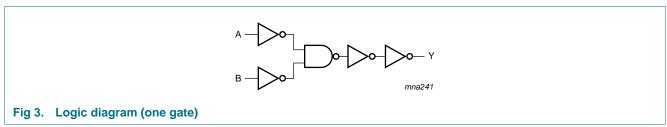
# 3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range Name		Description	Version					
74VHC32D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads;	SOT108-1					
74VHCT32D-Q100			body width 3.9 mm						
74VHC32PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package;	SOT402-1					
74VHCT32PW-Q100			14 leads; body width 4.4 mm						
74VHC32BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced	SOT762-1					
74VHCT32BQ-Q100			very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm						

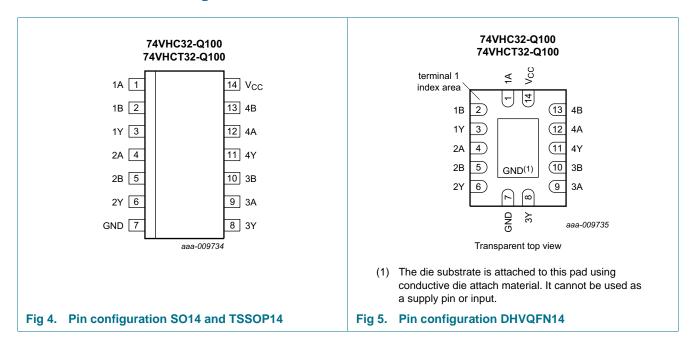
# 4. Functional diagram





# 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

I GOIO Z.	i iii accomptioni	
Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
$V_{CC}$	14	supply voltage

# 6. Functional description

Table 3. Function table[1]

Input	Output	
nA	nB	nY
L	L	L
X	Н	Н
Н	X	Н

<sup>[1]</sup> H = HIGH voltage level;

L = LOW voltage level;

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		, ,			,
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_1 < -0.5 \text{ V}$	<u>[1]</u> –20	-	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> –20	+20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I <sub>CC</sub>	supply current		-	+75	mA
$I_{GND}$	ground current		<b>-75</b>	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C	[2] _	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# 8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74VHC3	2-Q100					
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

74VHC\_VHCT32\_Q100

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2013. All rights reserved.

X = don't care.

<sup>[2]</sup> For SO14 packages: above 70 °C the value of P<sub>tot</sub> derates linearly at 8 mW/K. For TSSOP14 packages: above 60 °C the value of P<sub>tot</sub> derates linearly at 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P<sub>tot</sub> derates linearly at 4.5 mW/K.

 Table 5.
 Operating conditions ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74VHCT	32-Q100					
$V_{CC}$	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

## 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74VHC3	2-Q100				I			1		
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 3.0 \text{ V}$	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 3.0 \text{ V}$	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$								
output voltage	output voltage	$I_{O} = -50 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -50 \mu A; V_{CC} = 3.0 V$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_{O} = -50 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I <sub>I</sub>	input leakage current	$V_1 = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μΑ
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	pF

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74VHCT	32-Q100									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
output voltage	$I_{O} = -50 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V	
		$I_0 = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
OL	V <sub>OL</sub> LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
		$I_O = 50 \mu A$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
II	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	20	-	40	μΑ
Δl <sub>CC</sub>	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$ ; other pins at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C <sub>I</sub>	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
Co	output capacitance		-	4	-	-	-	-	-	pF

# 10. Dynamic characteristics

 Table 7.
 Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see <u>Figure 7</u>.

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
74VHC3	2-Q100	'		'	•	'				•
t <sub>pd</sub>	propagation delay	nA, nB to nY; see Figure 6 [2]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$								
		C <sub>L</sub> = 15 pF	-	3.9	7.9	1.0	9.5	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	5.6	11.4	1.0	13	1.0	14.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$								
		C <sub>L</sub> = 15 pF	-	2.8	5.5	1.0	6.5	1.0	7.0	ns
		C <sub>L</sub> = 50 pF	-	4.1	7.5	1.0	8.5	1.0	9.5	ns
C <sub>PD</sub>	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	-	10	-	-	-	-	-	pF

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 7.

Symbol Parameter Conditions		Conditions		25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			ı	Min	Typ[1]	Max	Min	Max	Min	Max	
74VHCT32-Q100; V <sub>CC</sub> = 4.5 V to 5.5 V											
t <sub>pd</sub>	propagation delay	nA, nB to nY; see Figure 6	[2]								
		C <sub>L</sub> = 15 pF		-	3.1	6.9	1.0	8.0	1.0	9.0	ns
		C <sub>L</sub> = 50 pF		-	4.3	7.9	1.0	9.0	1.0	10.0	ns
C <sub>PD</sub>	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]	-	12	-	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage ( $V_{CC} = 3.3 \text{ V}$  and  $V_{CC} = 5.0 \text{ V}$ ).
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$ 

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

### 11. Waveforms

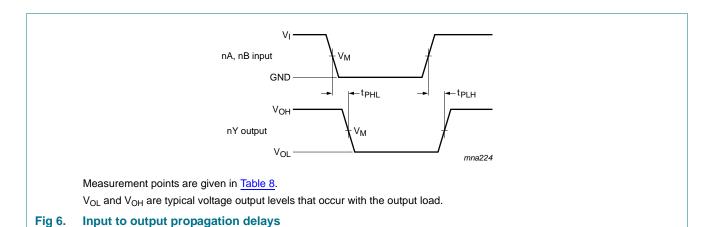
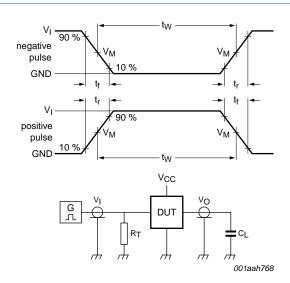


Table 8. Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74VHC32-Q100	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
74VHCT32-Q100	1.5 V	0.5V <sub>CC</sub>



Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $C_L$  = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

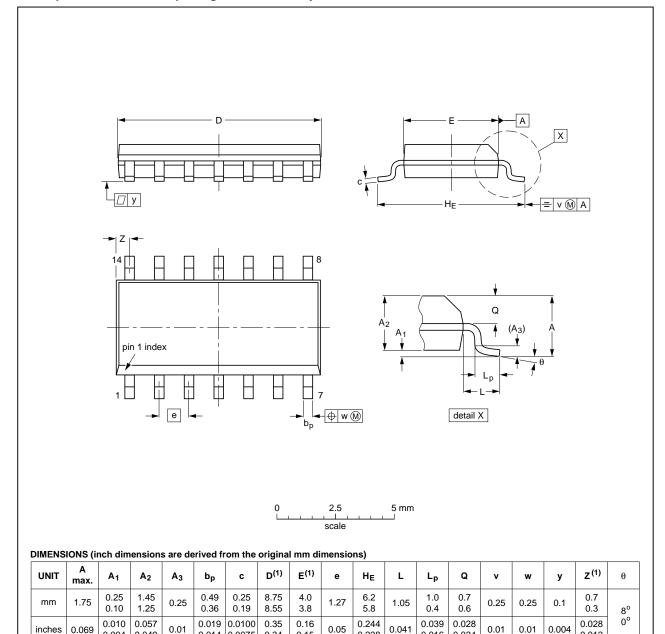
Table 9. Test data

Туре	Input		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74VHC32-Q100	V <sub>CC</sub>	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74VHCT32-Q100	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

# 12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



# Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.014

0.0075

0.34

0.15

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19

0.228

0.016

0.024

Package outline SOT108-1 (SO14)

0.004

0.049

74VHC\_VHCT32\_Q100

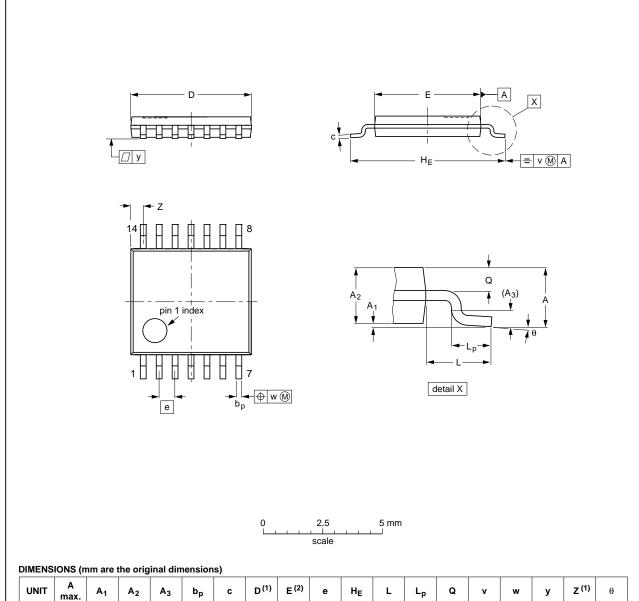
All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2013. All rights reserved.

0.012

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



	_																	
UNIT	max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				<del>-99-12-27</del> 03-02-18	
						-	î

Fig 9. Package outline SOT402-1 (TSSOP14)

74VHC\_VHCT32\_Q100

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2013. All rights reserved.

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

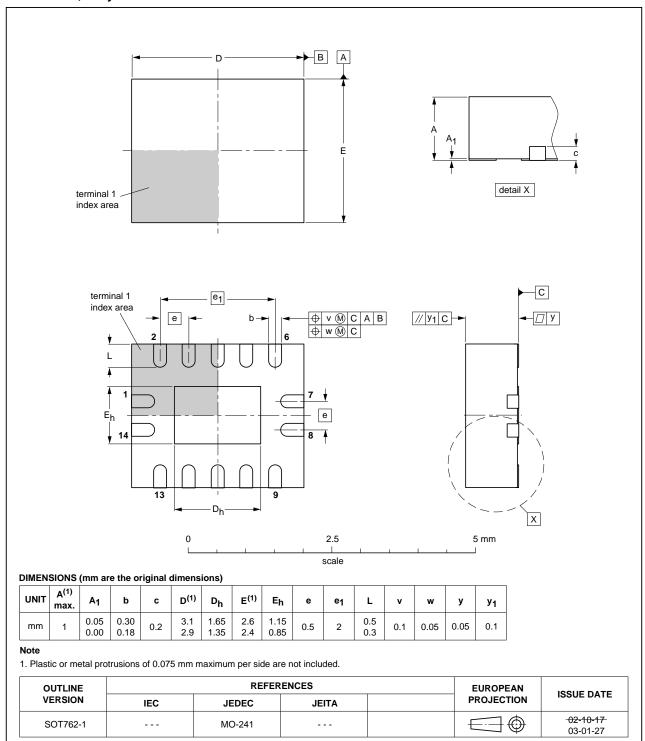


Fig 10. Package outline SOT762-1 (DHVQFN14)

## 13. Abbreviations

#### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MIL	Military
MM	Machine Model

# 14. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74VHC_VHCT32_Q100 v.1	20131220	Product data sheet	-	-

### 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for

inclusion and/or use of NXP Semiconductors products in such equipment or

applications and therefore such inclusion and/or use is at the customer's own

Suitability for use in automotive applications — This NXP

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

74VHC\_VHCT32\_Q100

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### 15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### 16. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

### 17. Contents

1	General description
2	Features and benefits
3	Ordering information
4	Functional diagram 2
5	Pinning information 3
5.1	Pinning
5.2	Pin description
6	Functional description 4
7	Limiting values 4
8	Recommended operating conditions 4
9	Static characteristics 5
10	Dynamic characteristics 6
11	Waveforms
12	Package outline
13	Abbreviations
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks14
16	Contact information 14
17	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

# NXP:

74VHCT32PW-Q100J 74VHCT32BQ-Q100X 74VHC32D-Q100J 74VHCT32D-Q100J 74VHC32PW-Q100J